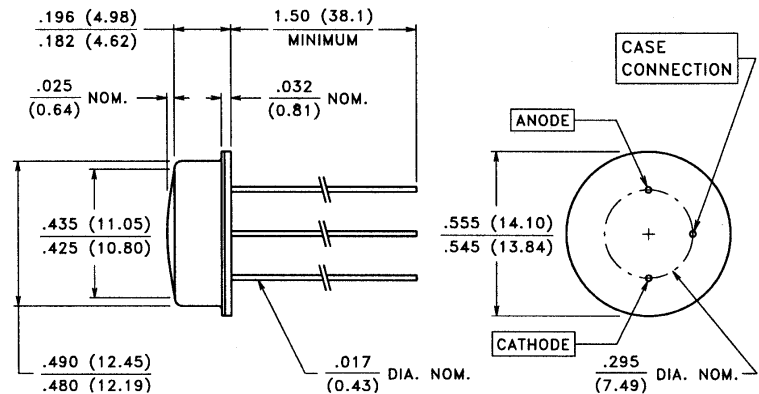


PACKAGE DIMENSIONS inch (mm)



CASE 15 TO-8 HERMETIC
CHIP ACTIVE AREA: .058 in² (37.7 mm²)

PRODUCT DESCRIPTION

Large area planar silicon photodiode in a “flat” window, three lead TO-8 package. Chip is isolated from case. The third lead allows case to be grounded. These diodes have very high shunt resistance and have good blue response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C
Operating Temperature: -40°C to 110°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | VTB6061J | | | UNITS |
|--------------------|---|-------------------------------|----------|--------------------------------|------|-----------|
| | | | Min. | Typ. | Max. | |
| I _{SC} | Short Circuit Current | H = 100 fc, 2850 K | 260 | 350 | | μA |
| TC I _{SC} | I _{SC} Temperature Coefficient | 2850 K | | .12 | .23 | %/°C |
| V _{OC} | Open Circuit Voltage | H = 100 fc, 2850 K | | 490 | | mV |
| TC V _{OC} | V _{OC} Temperature Coefficient | 2850 K | | -2.0 | | mV/°C |
| I _D | Dark Current | H = 0, V _R = 2.0 V | | | 2.0 | nA |
| R _{SH} | Shunt Resistance | H = 0, V = 10 mV | | .10 | | GΩ |
| TC R _{SH} | R _{SH} Temperature Coefficient | H = 0, V = 10 mV | | -8.0 | | %/°C |
| C _J | Junction Capacitance | H = 0, V = 0 | | 8.0 | | nF |
| S _R | Sensitivity | 365 nm | | 0.1 | | A/W |
| λ _{range} | Spectral Application Range | | 320 | | 1100 | nm |
| λ _p | Spectral Response - Peak | | | 920 | | nm |
| V _{BR} | Breakdown Voltage | | 2 | 40 | | V |
| θ _{1/2} | Angular Resp. - 50% Resp. Pt. | | | ±55 | | Degrees |
| NEP | Noise Equivalent Power | | | 5.7 x 10 ⁻¹⁴ (Typ.) | | W/√Hz |
| D* | Specific Detectivity | | | 1.1 x 10 ¹³ (Typ.) | | cm√Hz / W |